

Si Photo-diode Chip—TK0N60PDN

1. Scope

- The specification applies to NIP silicon photo-diode chips.
- Type : TK0N60PDN

2. Structure

- NIP planar type.
- Electrode topside (cathode) : Aluminum.
backside (anode) : Gold.

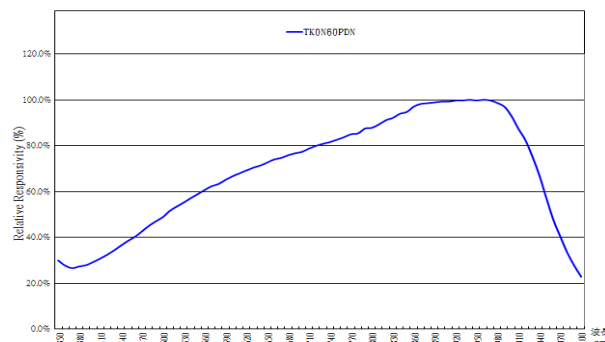
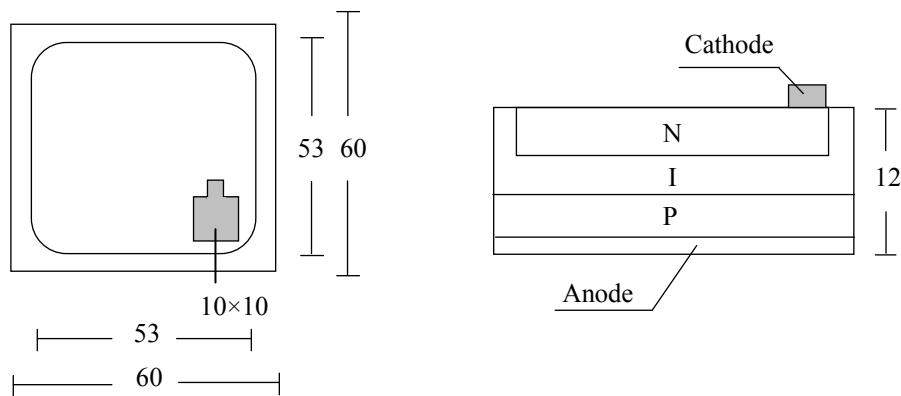
3. Size

- Chip size : 60mil × 60mil ± 1.5mil (1.520mm × 1.520mm ± 0.038mm)
- Thickness : 12mil ± 1mil (0.300mm ± 0.025mm)
- Active area : 53mil × 53mil ± 0.5mil (1.350mm × 1.350mm ± 0.013mm)
- Pad size : 10mil × 10mil ± 0.4mil (0.250mm × 0.250mm ± 0.01mm)
- Pattern drawing : per fig. 1

4. Electro-Optical Characteristics

(T_a = +25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit.
Forward Voltage	V _F	I _F =10mA, H=0	0.5		1.3	V
Reverse Breakdown Voltage	V _{BR}	I _R =100μA, H=0	35			V
Reverse Dark Current	I _D	V _R =10V, H=0			10	nA
Light Current	I _L	V _R =5V, Has 1mw/cm ² @940nm	57			μA
Peak Sensing Wavelength	λ _p			940		nm
Junction Capacitance	C _J	V _R =3V, F=1MHz		12		pF



Unit : mil

fig. 1

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